

**DISPOSABLE SPACER FOR SYMMETRIC AND ASYMMETRIC
SCHOTTKY CONTACT TO SOI MOSFET**

ABSTRACT OF THE DISCLOSURE

5 A silicon on insulator transistor is disclosed which has a Schottky contact to the
body. The Schottky contact may be formed on the source and/or drain side of the gate
conductor. A spacer, with at least a part thereof being disposable, is formed on the
sidewalls of the gate conductor. Extension regions are provided in the substrate which
extend under the spacer and the gate conductor. Source and drain diffusion regions are
implanted into the substrate adjacent to the extension regions. The disposable part of the
10 spacer is then removed to expose a portion of the extension region. A metal layer is
formed at least in the extension regions, resulting in the Schottky contact.